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PMZB300XN

20 V, single N-channel Trench MOSFET

1 August 2012

Product data sheet

1. Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Fast switching
- Trench MOSFET technology
- Low threshold voltage
- Ultra thin package profile of 0.37mm height

1.3 Applications

- · Relay driver
- · High-speed line driver
- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	20	V
V _{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	-	1	Α
Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I_D = 200 mA; T_j = 25 °C		-	0.3	0.38	Ω

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².





20 V, single N-channel Trench MOSFET

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	1 🔲	D ±
2	S	source	2 3	
3	D	drain	Transparent top view	G 1341
			DFN1006B-3 (SOT883B)	017aaa253

3. Ordering information

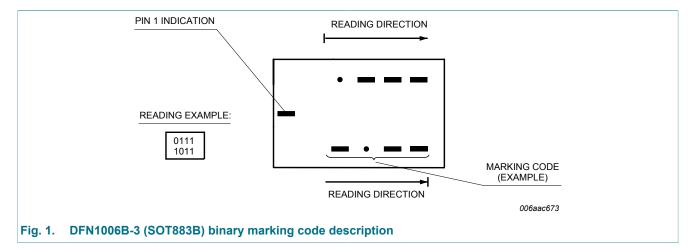
Table 3. Ordering information

Type number	Package	le e				
	Name	Description	Version			
PMZB300XN	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B			

4. Marking

Table 4. Marking codes

Type number	Marking code
PMZB300XN	0000 0111



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5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	20	V
V _{GS}	gate-source voltage			-12	12	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	1	Α
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	0.6	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	4	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	360	mW
			[1]	-	715	mW
		T _{sp} = 25 °C		-	2700	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	diode		1		'	,
I _S	source current	T _{amb} = 25 °C	[1]	-	670	mA

- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

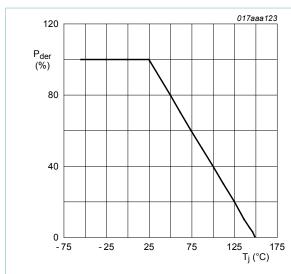


Fig. 2. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

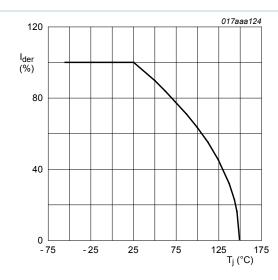


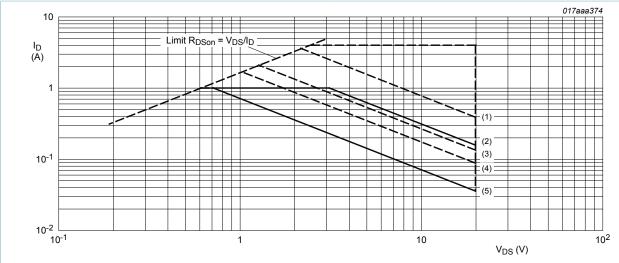
Fig. 3. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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I_{DM} = single pulse

- (1) $t_p = 1 \text{ ms}$
- (2) DC; T_{sp} = 25 °C
- (3) $t_p = 10 \text{ ms}$
- (4) $t_p = 100 \text{ ms}$
- (5) DC; $T_{amb} = 25 \, ^{\circ}C$; drain mounting pad 1 cm²

Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient		in free air	[1]	-	305	360	K/W
		[2]	-	150	175	K/W	
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	40	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

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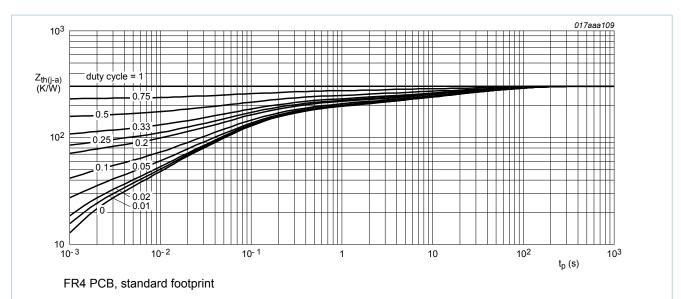


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

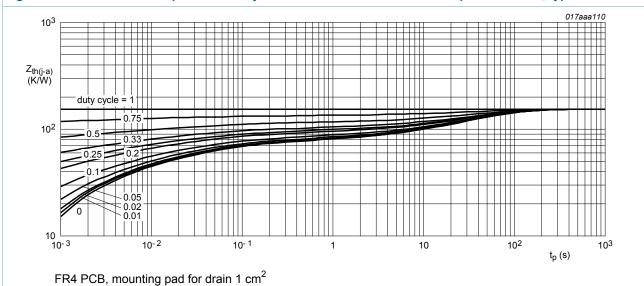


Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 10 \mu A; V_{GS} = 0 V; T_j = 25 °C$		20	-	-	V
V_{GSth}	gate-source threshold voltage	I_D = 250 μ A; V_{DS} = V_{GS} ; T_j = 25 °C		0.5	1	1.5	V
I _{DSS}	drain leakage current	V_{DS} = 20 V; V_{GS} = 0 V; T_j = 25 °C		-	-	1	μA
		V _{DS} = 20 V; V _{GS} = 0 V; T _j = 150 °C		-	-	100	μA
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{GSS}	gate leakage current	V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	0.1	μA
		V _{GS} = -12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	0.1	μA
Doon	drain-source on-state	V_{GS} = 4.5 V; I_{D} = 200 mA; T_{j} = 25 °C	-	0.3	0.38	Ω
	resistance	V_{GS} = 4.5 V; I_{D} = 200 mA; T_{j} = 150 °C	-	0.54	0.68	Ω
		V_{GS} = 2.5 V; I_{D} = 100 mA; T_{j} = 25 °C	-	0.47	0.55	mΩ
g _{fs}	forward transconductance	$V_{DS} = 5 \text{ V}; I_{D} = 200 \text{ mA}; T_{j} = 25 \text{ °C}$	-	1500	-	mS
Dynamic cl	haracteristics		'			
Q _{G(tot)}	total gate charge	V_{DS} = 10 V; I_{D} = 1 A; V_{GS} = 4.5 V; T_{j} = 25 °C	-	0.72	0.94	nC
Q _{GS}	gate-source charge		-	0.18	-	nC
Q_{GD}	gate-drain charge		-	0.18	-	nC
C _{iss}	input capacitance	V _{DS} = 20 V; f = 1 MHz; V _{GS} = 0 V;	-	34	51	pF
Coss	output capacitance	T _j = 25 °C	-	12	-	pF
C _{rss}	reverse transfer capacitance		-	8	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 10 V; R_L = 10 Ω ; V_{GS} = 4.5 V;	-	5	10	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	11	-	ns
$t_{d(off)}$	turn-off delay time		-	11	22	ns
t _f	fall time		-	6	-	ns
Source-dra	in diode		'			
V _{SD}	source-drain voltage	I_S = 300 mA; V_{GS} = 0 V; T_j = 25 °C	-	0.77	1.2	V

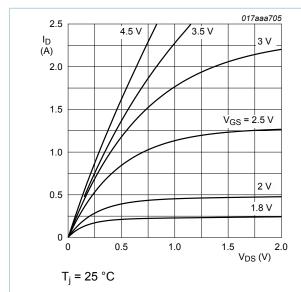


Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values

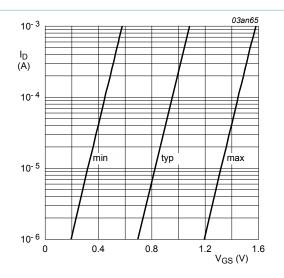


Fig. 8. Subthreshold drain current as a function of gate-source voltage

$$T_j = 25^{\circ}C; V_{DS} = 5V$$

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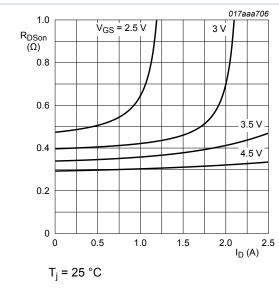


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

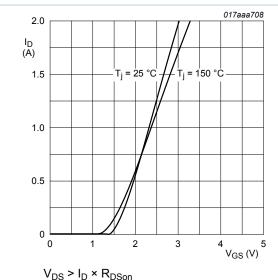


Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

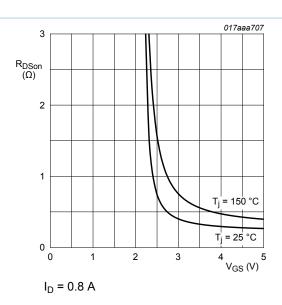


Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

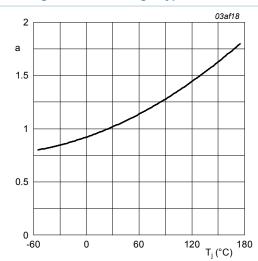


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

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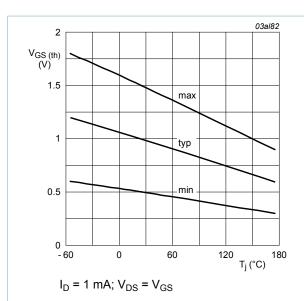


Fig. 13. Gate-source threshold voltage as a function of junction temperature

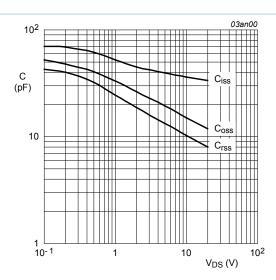


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V; f = 1MHz$$

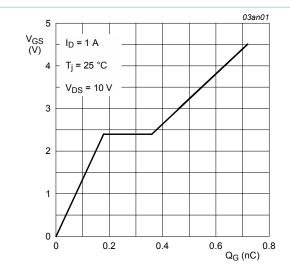


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$$I_D=1A; V_{DS}=10V$$

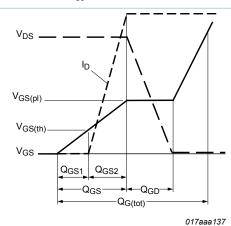
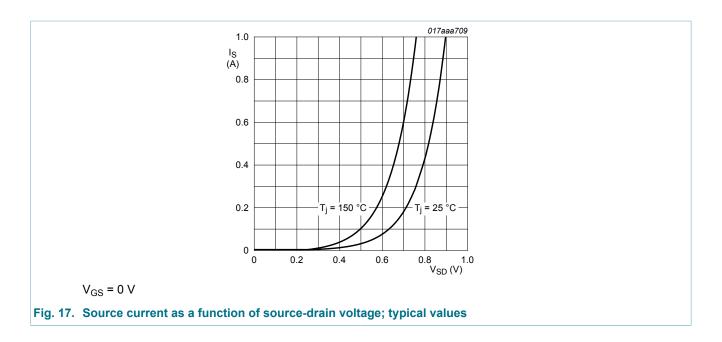
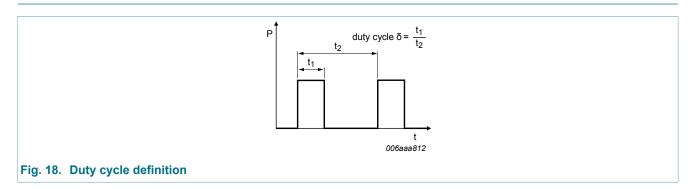


Fig. 16. Gate charge waveform definitions

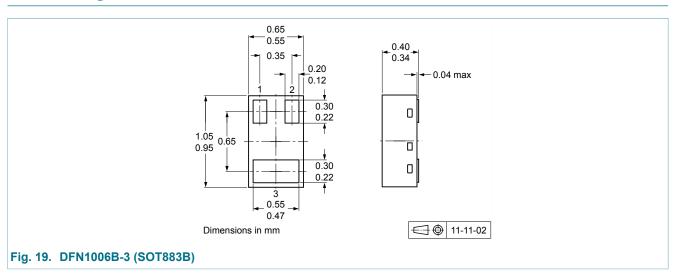
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8. Test information



9. Package outline

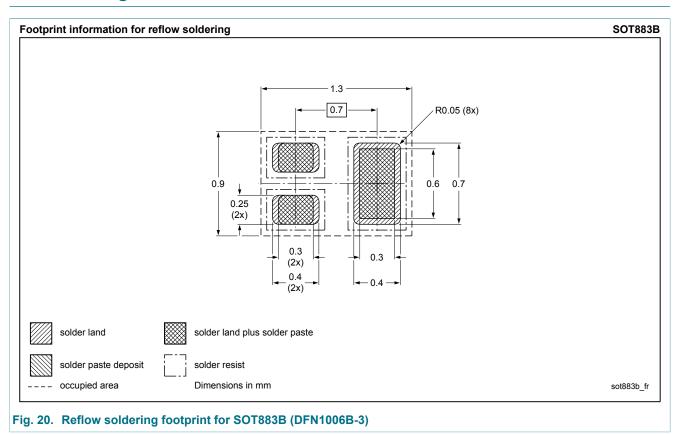


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10. Soldering



11. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMZB300XN v.1	20120801	Product data sheet	-	-

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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
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Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Date of release: 1 August 2012

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